

#### **Description**

The PHKD6N02LT,518 uses advanced trench technology to provide excellent R<sub>DS(ON)</sub>, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

## D1b1<sub>D2</sub> D2 S1<sub>G1</sub> S2<sub>G2</sub>

SOP-8 (SOIC-8)

#### **General Features**

 $V_{DS} = 20V I_{D} = 6A$ 

 $R_{DS(ON)} < 25m\Omega$  @  $V_{GS}=4.5V$ 

# D1 D1 D2 E

#### **Application**

**Battery protection** 

Load switch

Uninterruptible power supply

#### **Dual N-Channel MOSFET**

#### **Package Marking and Ordering Information**

Product ID	Pack	Brand	Qty(PCS)
PHKD6N02LT,518	SOP-8(SOIC-8)	HXY MOSFET	3000

#### Absolute Maximum Ratings@Tj=25°C(unless otherwise specified)

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	20	V
V <sub>G</sub> s	Gate-Source Voltage	<u>+</u> 12	V
I <sub>D</sub> @T <sub>A</sub> =25°C	Drain Current, V <sub>GS</sub> @ 4.5V <sup>3</sup>	6	А
I <sub>D</sub> @T <sub>A</sub> =70°C	Drain Current, V <sub>GS</sub> @ 4.5V <sup>3</sup>	4.8	А
Ідм	Pulsed Drain Current <sup>1</sup>	26	А
Pd@Ta=25°C	Total Power Dissipation	2	W
	Linear Derating Factor	0.016	W/°C
Тѕтс	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C
Rthj-a	Maximum Thermal Resistance, Junction- ambient <sup>3</sup>	62.5	°C/W



### Electrical Characteristics@Tj=25°C(unless otherwise specified)

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Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	20	-	-	\
` '	Static Drain-Source On- Resistance <sup>2</sup>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =6A	-	21	25	mΩ
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =4A	-	32	45	mΩ
VGS(th)	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	-	1.2	3	V
<b>g</b> fs	Forward Transconductance	V <sub>DS</sub> =10V, I <sub>D</sub> =6A	-	6	-	S
IDSS	Drain-Source Leakage Current	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V	-	-	25	uA
	Drain-Source Leakage Current (T <sub>j</sub> =70°C)	V <sub>DS</sub> =20V ,V <sub>GS</sub> =0V	-	-	250	uA
Igss	Gate-Source Leakage	V <sub>GS</sub> = <u>+</u> 12V, V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA
$Q_g$	Total Gate Charge <sup>2</sup>	I <sub>D</sub> =6A	-	11	17.6	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =16V V <sub>GS</sub> =4.5V	-	1.1	-	nC
Qgd	Gate-Drain ("Miller") Charge		-	4.1	-	nC
t <sub>d(on)</sub>	Turn-on Delay Time <sup>2</sup>	V <sub>DS</sub> =10V	-	4.2	-	ns
tr	Rise Time	I <sub>D</sub> =1A R <sub>G</sub> =3.3Ω,V <sub>GS</sub> =10V R <sub>D</sub> =10Ω	-	9	-	ns
td(off)	Turn-off Delay Time		-	23	-	ns
tf	Fall Time	1052	-	3.5	-	ns
Ciss	Input Capacitance		-	570	910	pF
Coss	Output Capacitance	V <sub>GS</sub> =0V	-	90	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	V <sub>DS</sub> =20V f=1.0MHz	-	85	-	pF
R <sub>g</sub>	Gate Resistance	f=1.0MHz	-	1.6	2.4	Ω
V <sub>SD</sub>	Forward On Voltage <sup>2</sup>	I <sub>S</sub> =1.7A, V <sub>GS</sub> =0V	-	-	1.2	V
trr	Reverse Recovery Time <sup>2</sup>	Is=6A, V <sub>GS</sub> =0V,	-	21	-	ns
Qrr	Reverse Recovery Charge	dl/dt=100A/μs	-	14	-	nC
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#### Notes:

<sup>1.</sup> Pulse width limited by Max. junction temperature.

<sup>2.</sup>Pulse test

<sup>3.</sup>Surface mounted on 1 in₂ copper pad of FR4 board, t ≤10sec ; 135 °C/W when mounted on Min. copper pad.



#### **Typical Characteristics**

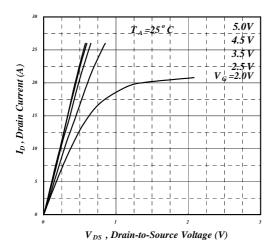


Fig 1. Typical Output Characteristics

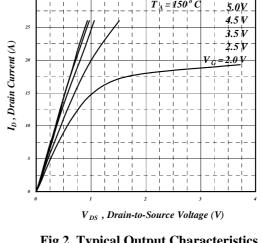


Fig 2. Typical Output Characteristics

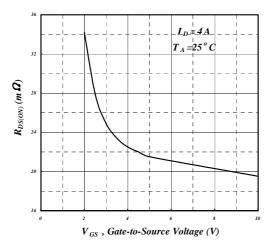


Fig 3. On-Resistance v.s. Gate Voltage

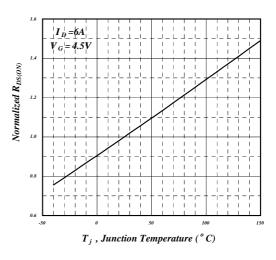


Fig 4. Normalized On-Resistance v.s. Temperature

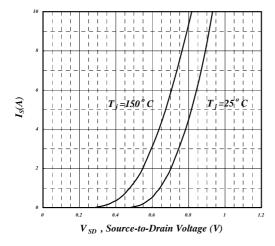


Fig 5. Forward Characteristic of **Reverse Diode** 

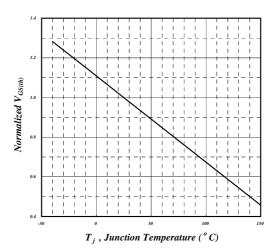


Fig 6. Gate Threshold Voltage v.s. **Junction Temperature** 



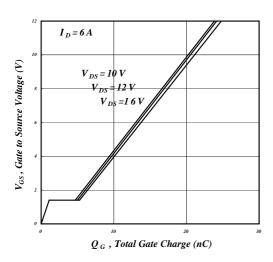


Fig 7. Gate Charge Characteristics

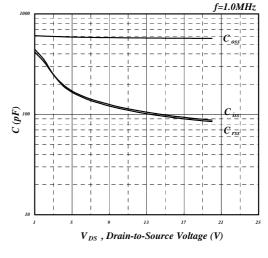


Fig 8. Typical Capacitance Characteristics

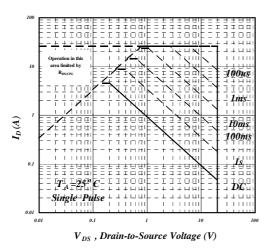


Fig 9. Maximum Safe Operating Area

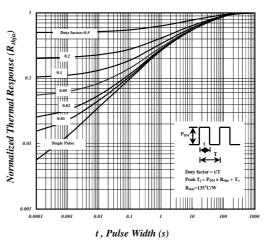


Fig 10. Effective Transient Thermal Impedance

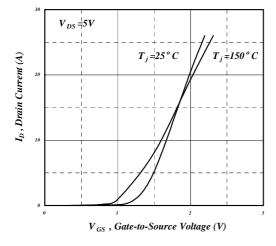


Fig 11. Transfer Characteristics

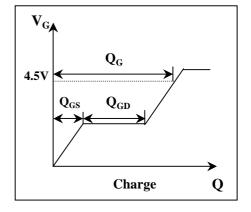
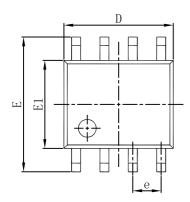
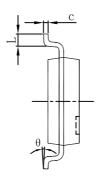


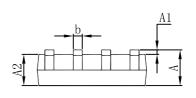
Fig 12. Gate Charge Waveform



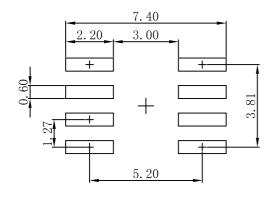
#### SOP-8(SOIC-8) Package Outline Dimensions







Symbol	Dimensions In Millimeters		Dimensions In Inches		
3y111001	Min	Max	Min	Max	
A	1.350	1.750	0.053	0.069	
A1	0.100	0. 250	0.004	0. 010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0. 020	
c	0.170	0.250	0.007	0.010	
D	4.800	5.000	0.189	0. 197	
e	1.270 (BSC)		0.050 (BSC)		
E	5.800	6. 200	0.228	0. 244	
E1	3.800	4.000	0.150	0. 157	
L	0.400	1.270	0.016	0.050	
θ	0°	8°	0°	8°	



- Note: 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
  3.The pad layout is for reference purposes only.

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